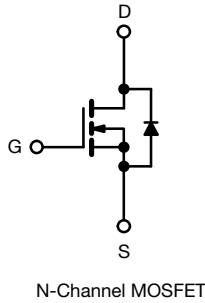
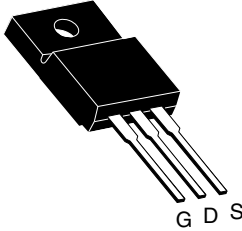


D Series Power MOSFET

TO-220 FULLPAK

FEATURES

- Optimal design
 - Low area specific on-resistance
 - Low input capacitance (C_{iss})
 - Reduced capacitive switching losses
 - High body diode ruggedness
 - Avalanche energy rated (UIS)
- Optimal efficiency and operation
 - Low cost
 - Simple gate drive circuitry
 - Low figure-of-merit (FOM): $R_{on} \times Q_g$
 - Fast switching
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912


RoHS*
Available

Note

* This datasheet provides information about parts that are RoHS-compliant and / or parts that are non RoHS-compliant. For example, parts with lead (Pb) terminations are not RoHS-compliant. Please see the information / tables in this datasheet for details

APPLICATIONS

- Consumer electronics
 - Displays (LCD or Plasma TV)
- Server and telecom power supplies
 - SMPS
- Industrial
 - Welding
 - Induction heating
 - Motor drives
- Battery chargers

PRODUCT SUMMARY	
V_{DS} (V) at T_J max.	550
$R_{DS(on)}$ max. (Ω) at 25 °C	$V_{GS} = 10$ V 0.28
Q_g max. (nC)	76
Q_{gs} (nC)	11
Q_{gd} (nC)	17
Configuration	Single

ORDERING INFORMATION	
Package	TO-220 FULLPAK
Lead (Pb)-free	SiHF18N50D-E3


ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)			
PARAMETER	SYMBOL	LIMIT	UNIT
Drain-source voltage	V_{DS}	500	V
Gate-source voltage	V_{GS}	± 30	
Gate-source voltage AC ($f > 1$ Hz)		30	
Continuous drain current ($T_J = 150$ °C) ^e	V_{GS} at 10 V	$T_C = 25$ °C	A
		$T_C = 100$ °C	
Pulsed drain current ^a	I_{DM}	53	
Linear derating factor		0.3	W/°C
Single pulse avalanche energy ^b	E_{AS}	115	mJ
Maximum power dissipation	P_D	39	W
Operating junction and storage temperature range	T_J, T_{stg}	-55 to +150	°C
Drain-source voltage slope	dV/dt	$T_J = 125$ °C	V/ns
Reverse diode dV/dt ^d		0.4	
Soldering recommendations (peak temperature) ^c	For 10 s	300	°C
Mounting torque	M3 screw	0.6	Nm

Notes

- Repetitive rating; pulse width limited by maximum junction temperature
- $V_{DD} = 50$ V, starting $T_J = 25$ °C, $L = 2.3$ mH, $R_g = 25$ Ω , $I_{AS} = 10$ A
- 1.6 mm from case
- $I_{SD} \leq I_D$, starting $T_J = 25$ °C
- Limited by maximum junction temperature



THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum junction-to-ambient	R_{thJA}	-	65	°C/W
Maximum junction-to-case (drain)	R_{thJC}	-	3.2	

SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-source breakdown voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$		500	-	-	V
V_{DS} temperature coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^\circ\text{C}, I_D = 250\text{ }\mu\text{A}$		-	0.58	-	V/°C
Gate threshold voltage (N)	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$		3.0	-	5.0	V
Gate-source leakage	I_{GSS}	$V_{GS} = \pm 30\text{ V}$		-	-	± 100	nA
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 500\text{ V}, V_{GS} = 0\text{ V}$		-	-	1	μA
		$V_{DS} = 400\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$		-	-	10	
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$	$I_D = 9\text{ A}$	-	0.23	0.28	Ω
Forward transconductance	g_{fs}	$V_{DS} = 50\text{ V}, I_D = 9\text{ A}$		-	6.4	-	S
Dynamic							
Input capacitance	C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 100\text{ V}, f = 1.0\text{ MHz}$		-	1500	-	pF
Output capacitance	C_{oss}			-	131	-	
Reverse transfer capacitance	C_{rss}			-	14	-	
Effective output capacitance, energy related ^a	$C_{o(er)}$	$V_{GS} = 0\text{ V}, V_{DS} = 0\text{ V to } 400\text{ V}$		-	113	-	
Effective output capacitance, time related ^b	$C_{o(tr)}$			-	164	-	
Total gate charge	Q_g	$V_{GS} = 10\text{ V}$	$I_D = 9\text{ A}, V_{DS} = 400\text{ V}$	-	38	76	nC
Gate-source charge	Q_{gs}			-	11	-	
Gate-drain charge	Q_{gd}			-	17	-	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 400\text{ V}, I_D = 9\text{ A}, V_{GS} = 10\text{ V}, R_g = 9.1\text{ }\Omega$		-	19	38	ns
Rise time	t_r			-	36	72	
Turn-off delay time	$t_{d(off)}$			-	36	72	
Fall time	t_f			-	30	60	
Gate input resistance	R_g	$f = 1\text{ MHz}, \text{open drain}$		-	1.7	-	Ω
Drain-Source Body Diode Characteristics							
Continuous source-drain diode current	I_S	MOSFET symbol showing the integral reverse P - N junction diode 	-	-	18	A	
Pulsed diode forward current	I_{SM}		-	-	72		
Diode forward voltage	V_{SD}	$T_J = 25\text{ }^\circ\text{C}, I_S = 9\text{ A}, V_{GS} = 0\text{ V}$		-	-	1.2	V
Reverse recovery time	t_{rr}	$T_J = 25\text{ }^\circ\text{C}, I_F = I_S = 9\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, V_R = 20\text{ V}$		-	354	-	ns
Reverse recovery charge	Q_{rr}			-	3.9	-	μC
Reverse recovery current	I_{RRM}			-	21	-	A

Notes

- a. $C_{oss(er)}$ is a fixed capacitance that gives the same energy as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DSS}
- b. $C_{oss(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DSS}



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

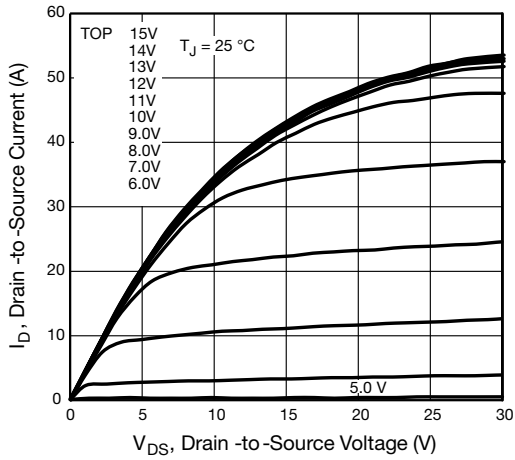


Fig. 1 - Typical Output Characteristics

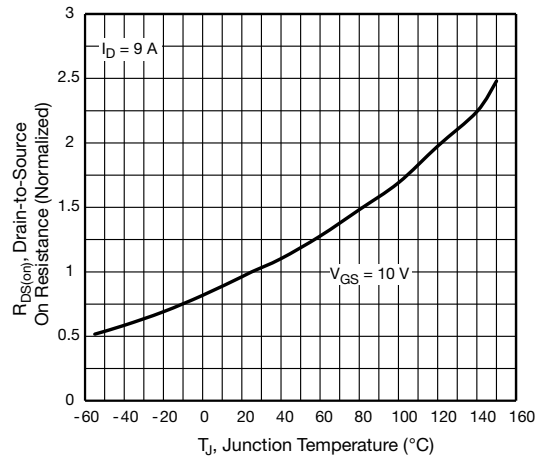


Fig. 4 - Normalized On-Resistance vs. Temperature

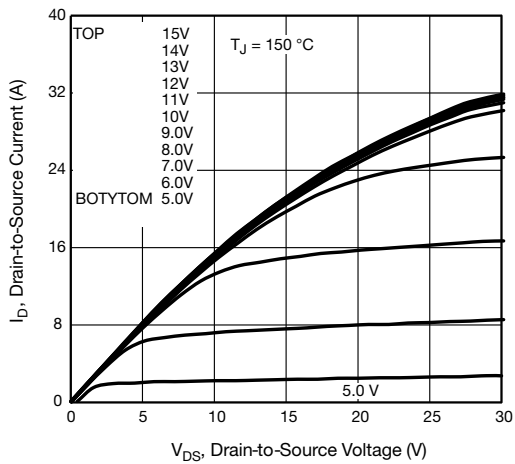


Fig. 2 - Typical Output Characteristics

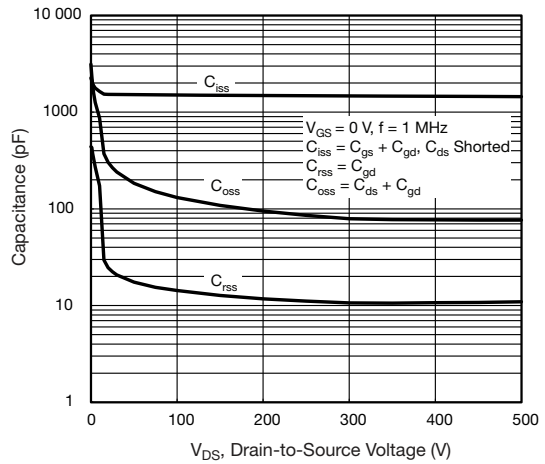


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

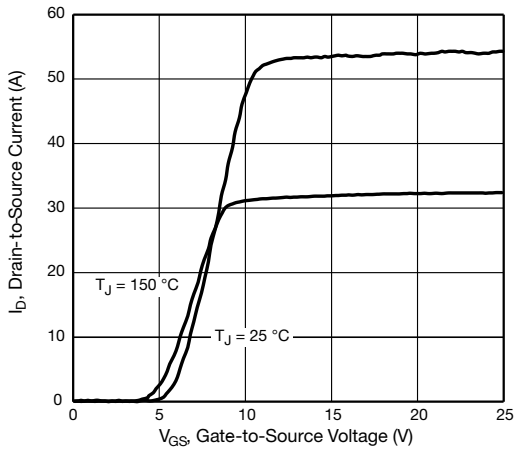


Fig. 3 - Typical Transfer Characteristics

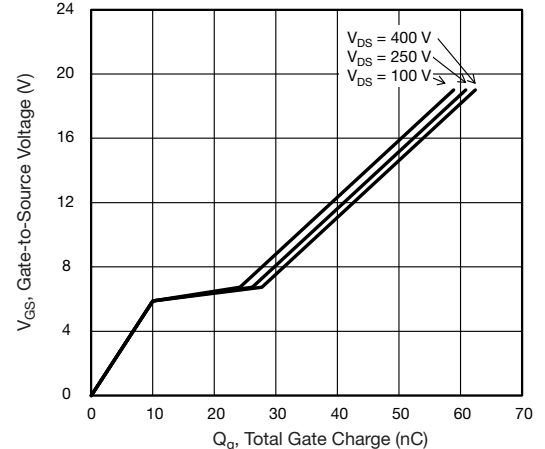


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

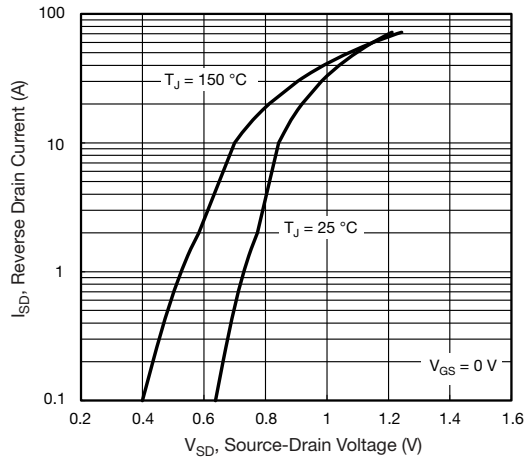


Fig. 7 - Typical Source-Drain Diode Forward Voltage

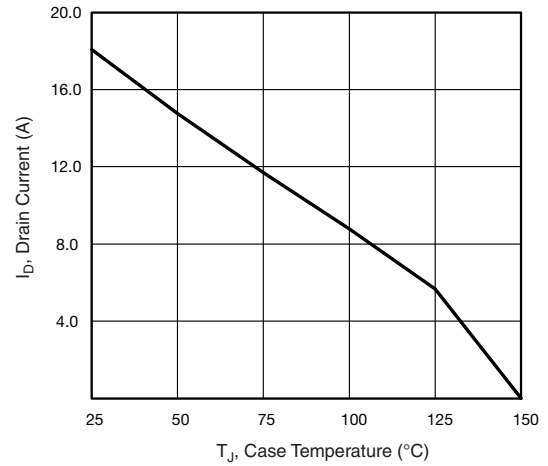


Fig. 9 - Maximum Drain Current vs. Case Temperature

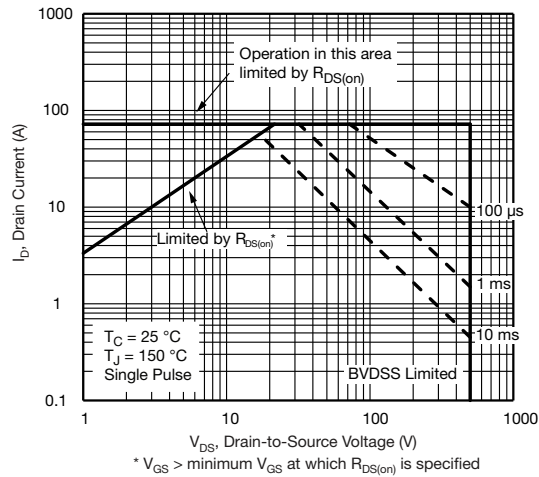


Fig. 8 - Maximum Safe Operating Area

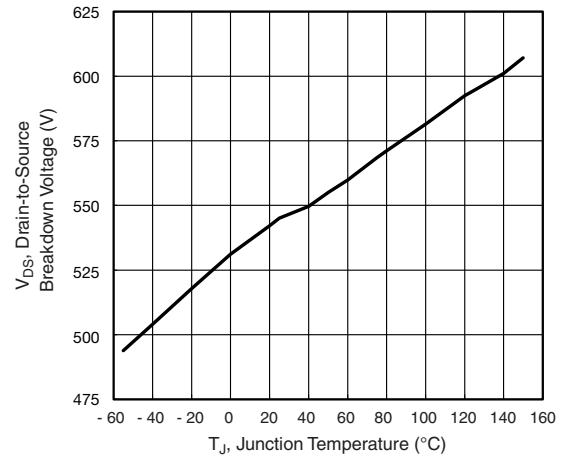


Fig. 10 - Typical Drain-to-Source Voltage vs. Temperature

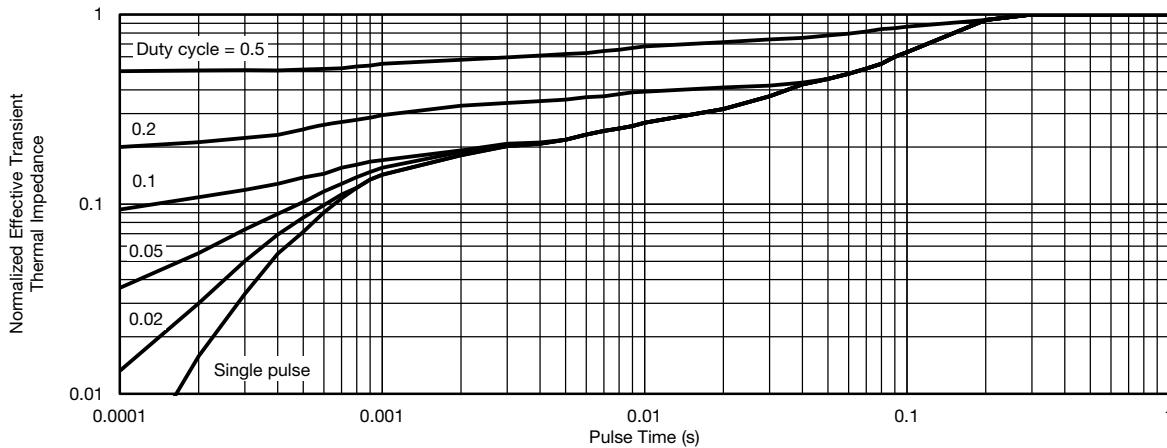


Fig. 11 - Normalized Thermal Transient Impedance, Junction-to-Case

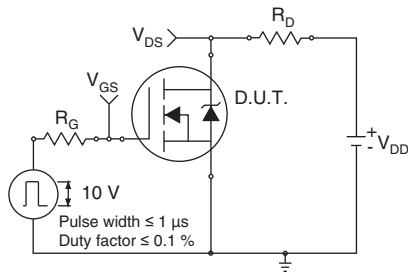


Fig. 12 - Switching Time Test Circuit

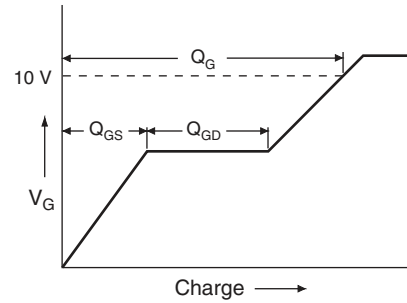


Fig. 16 - Basic Gate Charge Waveform

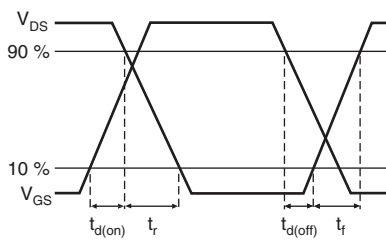


Fig. 13 - Switching Time Waveforms



Fig. 17 - Gate Charge Test Circuit

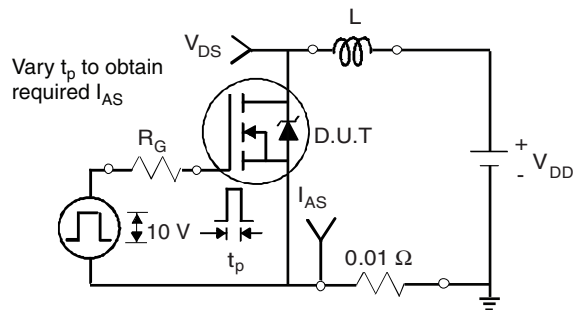


Fig. 14 - Unclamped Inductive Test Circuit

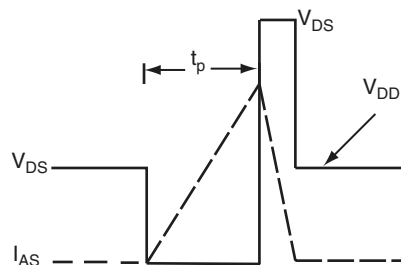
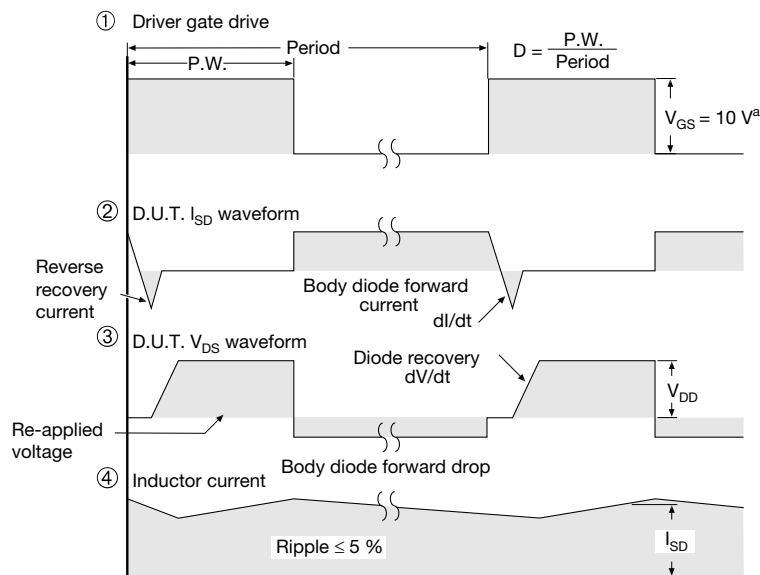


Fig. 15 - Unclamped Inductive Waveforms



Note

a. $V_{GS} = 5\text{ V}$ for logic level devices

Fig. 18 - For N-Channel

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TO-220 FULLPAK (HIGH VOLTAGE)



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.570	4.830	0.180	0.190
A1	2.570	2.830	0.101	0.111
A2	2.510	2.850	0.099	0.112
b	0.622	0.890	0.024	0.035
b2	1.229	1.400	0.048	0.055
b3	1.229	1.400	0.048	0.055
c	0.440	0.629	0.017	0.025
D	8.650	9.800	0.341	0.386
d1	15.88	16.120	0.622	0.635
d3	12.300	12.920	0.484	0.509
E	10.360	10.630	0.408	0.419
e	2.54 BSC		0.100 BSC	
L	13.200	13.730	0.520	0.541
L1	3.100	3.500	0.122	0.138
n	6.050	6.150	0.238	0.242
Ø P	3.050	3.450	0.120	0.136
u	2.400	2.500	0.094	0.098
v	0.400	0.500	0.016	0.020

ECN: X09-0126-Rev. B, 26-Oct-09
 DWG: 5972

Notes

1. To be used only for process drawing.
2. These dimensions apply to all TO-220, FULLPAK leadframe versions 3 leads.
3. All critical dimensions should C meet $C_{pk} > 1.33$.
4. All dimensions include burrs and plating thickness.
5. No chipping or package damage.



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